

Description

JMT N And P-Channel Enhancement Mode MOSFET

Features

- N-Channel: 40V, 14A
 $R_{DS(ON)} < 22m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 28m\Omega @ V_{GS} = -4.5V$
- P-Channel: -40V, -14A
 $R_{DS(ON)} < 50m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 70m\Omega @ V_{GS} = -4.5V$
- Excellent Gate Charge x $R_{DS(ON)}$ Product(FOM)
- Very Low On-resistance $R_{DS(ON)}$
- Fast Switching Speed

Application

- Battery Protection
- Load Switch
- Power Management



100% UIS TESTED!
100% ΔVds TESTED!

Top View Bottom View

PDFN3.3X3.3-8L(Dual)

Q170C04D
XXXXX XXX

Marking and pin Assignment

Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
Q170C04D	JMTQ170C04D	TAPING	PDFN3.3X3.3-8L	13inch	5000	50000

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Max. N-Channel	Max. P-Channel	Units
V _{DSS}	Drain-Source Voltage	40	-40	V
V _{GSS}	Gate-Source Voltage	±20	±20	V
I _D	Continuous Drain Current	T _C = 25°C	-14	A
		T _C = 100°C	-9	A
I _{DM}	Pulsed Drain Current ^{note1}	56	-56	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}	16	25	mJ
P _D	Power Dissipation	T _C = 25°C	17	W
R _{θJA}	Thermal Resistance, Junction to Case	17	7.3	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C



N-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =10V, I _D =14A	-	16	22	mΩ
		V _{GS} =4.5V, I _D =10A	-	20	28	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1.0MHz	-	980	-	pF
C _{oss}	Output Capacitance		-	86.2	-	pF
C _{rss}	Reverse Transfer Capacitance		-	68.5	-	pF
Q _g	Total Gate Charge	V _{DS} =20V, I _D =8A, V _{GS} =10V	-	11	-	nC
Q _{gs}	Gate-Source Charge		-	1.9	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	2.2	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =20V, I _D =14A, R _L =2.5Ω, R _{REN} =3Ω	-	11	-	ns
t _r	Turn-on Rise Time		-	13	-	ns
t _{d(off)}	Turn-off Delay Time		-	36	-	ns
t _f	Turn-off Fall Time		-	9	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	14	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	56	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =14A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	T _J =25°C,	-	19	-	ns
Q _{rr}	Body Diode Reverse Recovery	I _F =14A, di/dt=100A/μs	-	11	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25°C, V_{DD}=20V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=8A

T_J=25°C, V_{DD}=-20V, V_G=-10V, L=0.5mH, R_g=25Ω, I_{AS}=-10A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



P-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -40V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} = -10V, I _D = -5A	-	38	50	mΩ
		V _{GS} = -4.5V, I _D = -3A	-	50	70	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -20V, V _{GS} =0V, f=1.0MHz	-	1034	-	pF
C _{oss}	Output Capacitance		-	107	-	pF
C _{rss}	Reverse Transfer Capacitance		-	79.5	-	pF
Q _g	Total Gate Charge	V _{DS} = -20V, I _D = -8A, V _{GS} = -10V	-	20	-	nC
Q _{gs}	Gate-Source Charge		-	3.5	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	4.2	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -20V, I _D = -14A, V _{GS} = -10V, R _{GEN} =2.5Ω	-	8	-	ns
t _r	Turn-on Rise Time		-	15	-	ns
t _{d(off)}	Turn-off Delay Time		-	23	-	ns
t _f	Turn-off Fall Time		-	9	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-14	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-56	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -14A	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =-14A, di/dt=100A/μs	-	29	-	ns
Q _{rr}	Reverse Recovery Charge		-	20	-	nC



Typical Performance Characteristics-N

Figure 1: Output Characteristics

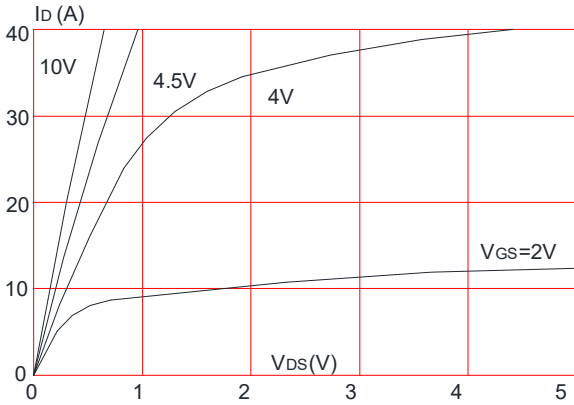


Figure 2: Typical Transfer Characteristics

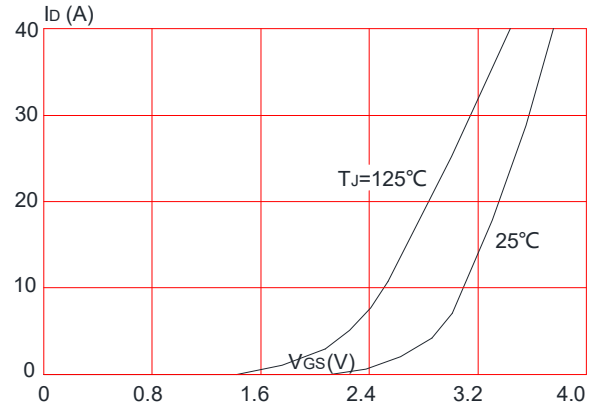


Figure 3: On-resistance vs. Drain Current

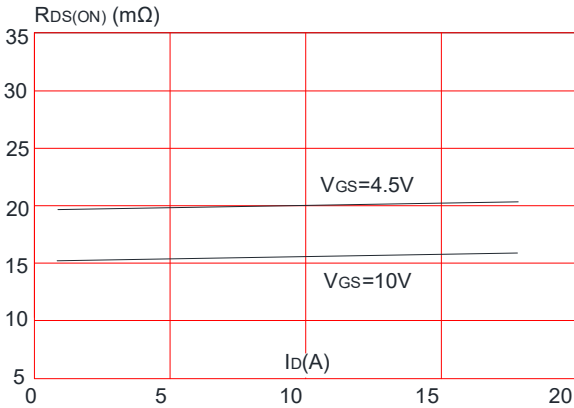


Figure 4: Body Diode Characteristics

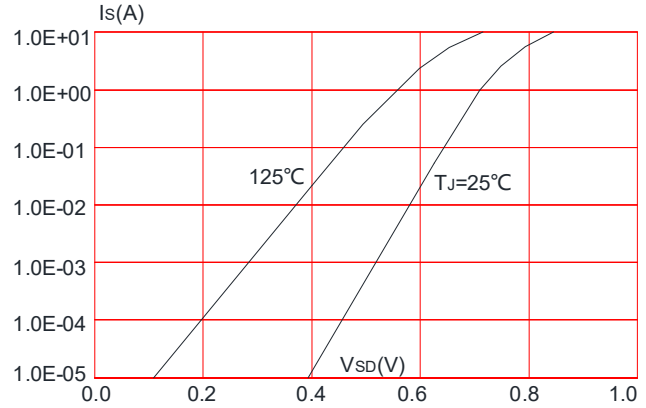


Figure 5: Gate Charge Characteristics

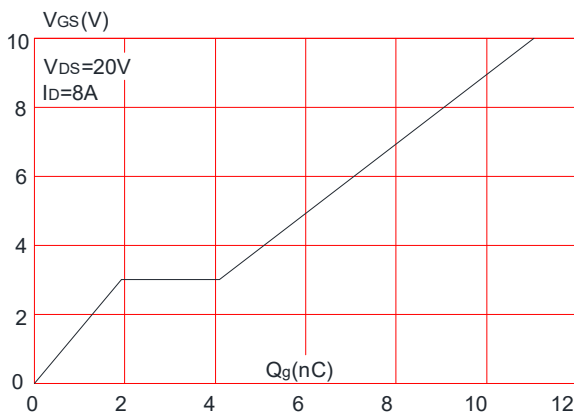


Figure 6: Capacitance Characteristics

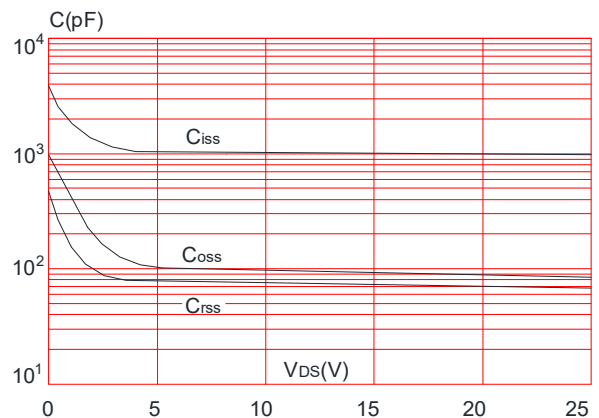




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

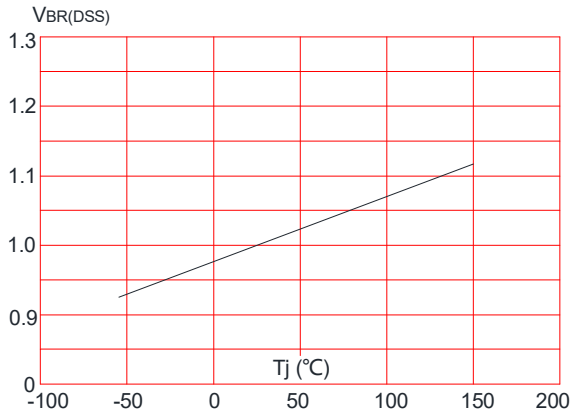


Figure 8: Normalized on Resistance vs. Junction Temperature

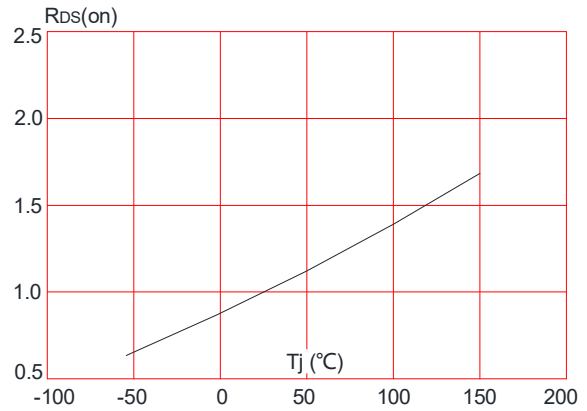


Figure 9: Maximum Safe Operating Area

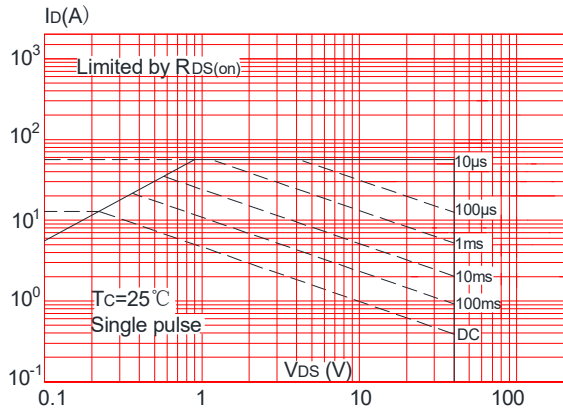


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

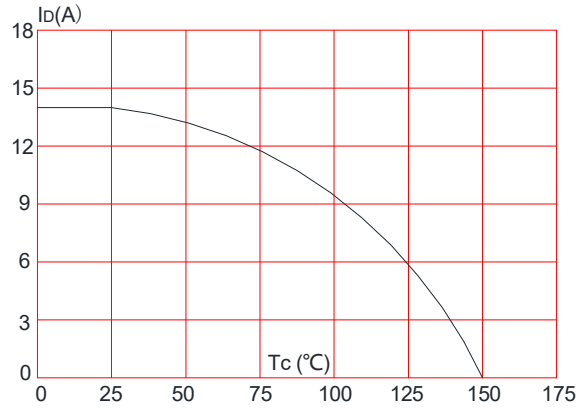
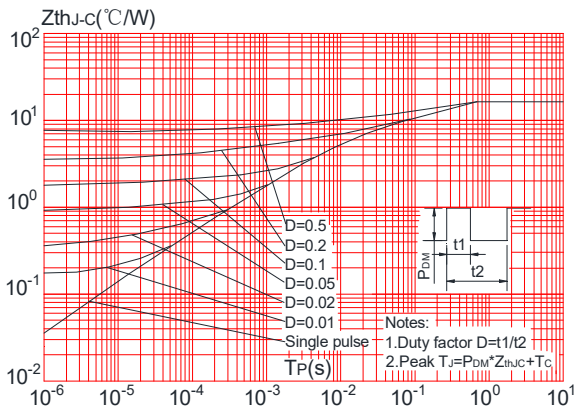


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit-N

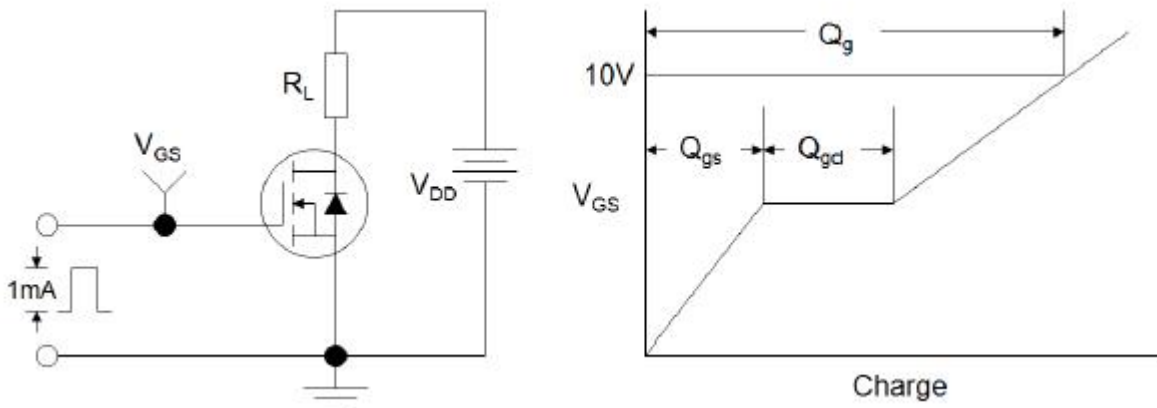


Figure1:Gate Charge Test Circuit & Waveform

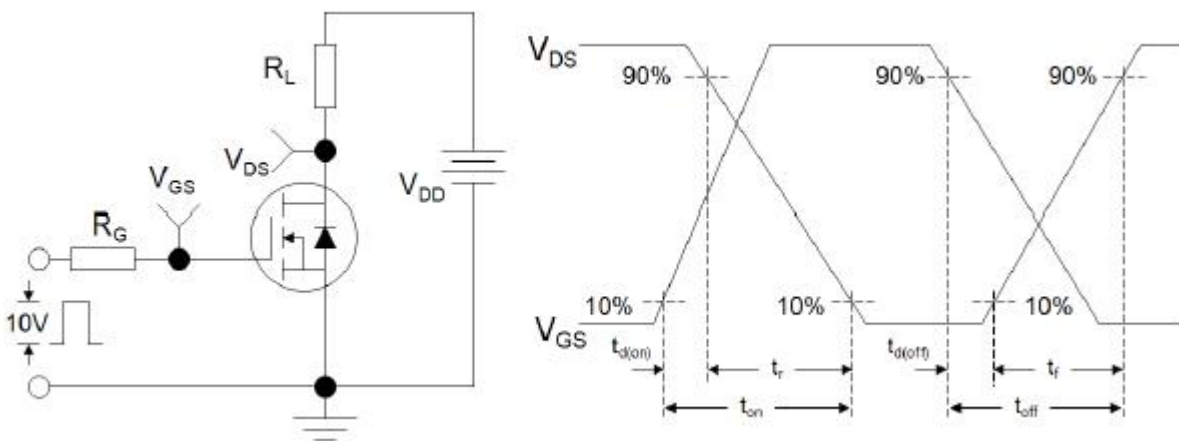


Figure 2: Resistive Switching Test Circuit & Waveforms

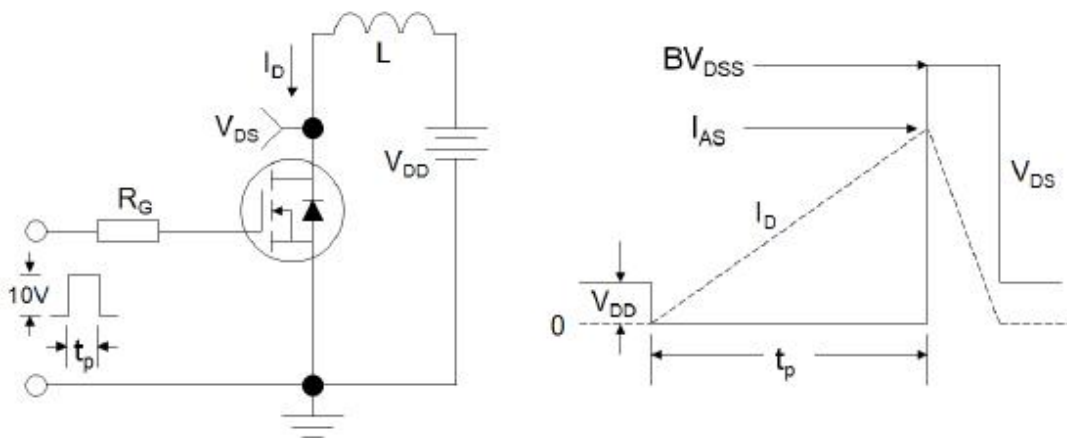


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



Typical Performance Characteristics-P

Figure 1: Output Characteristics

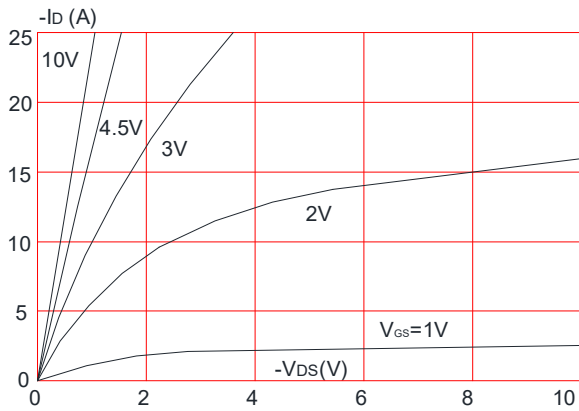


Figure 2: Typical Transfer Characteristics

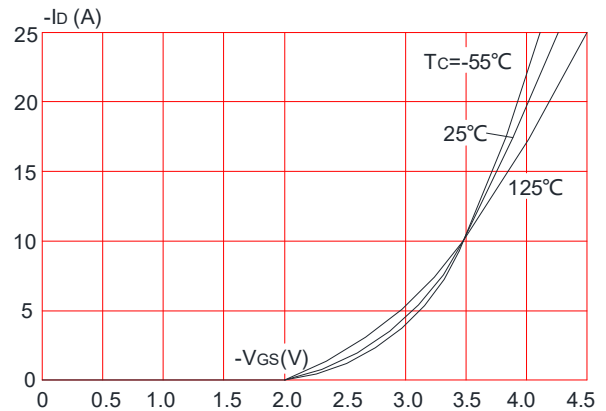


Figure 3: On-resistance vs. Drain Current

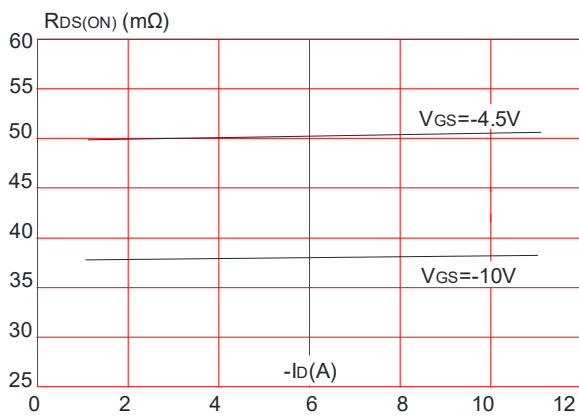


Figure 4: Body Diode Characteristics

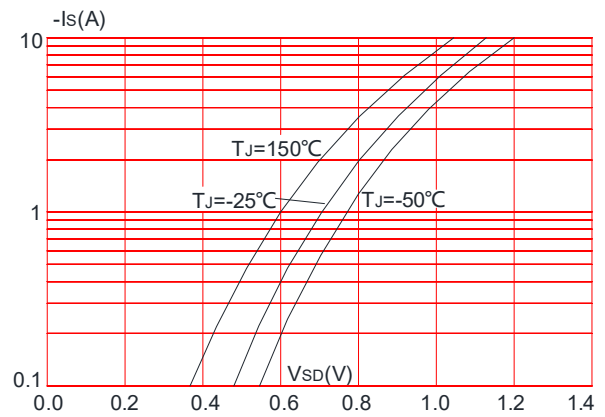


Figure 5: Gate Charge Characteristics

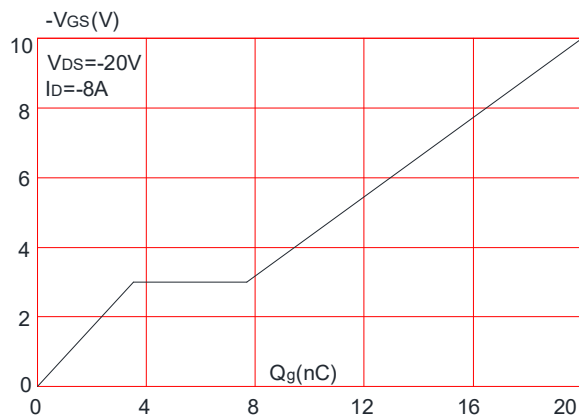


Figure 6: Capacitance Characteristics

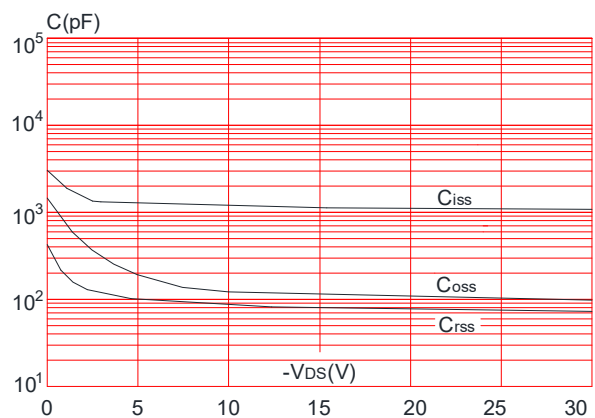




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

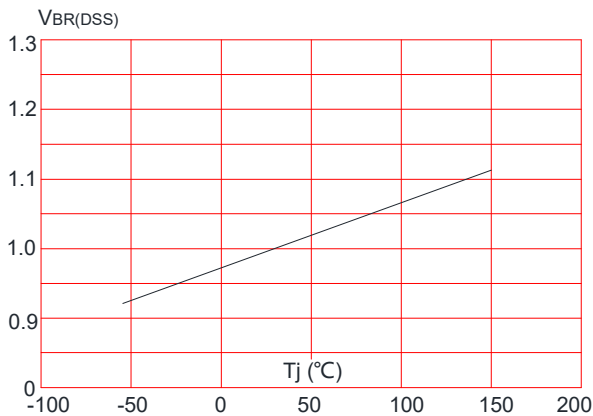


Figure 8: Normalized on Resistance vs. Junction Temperature

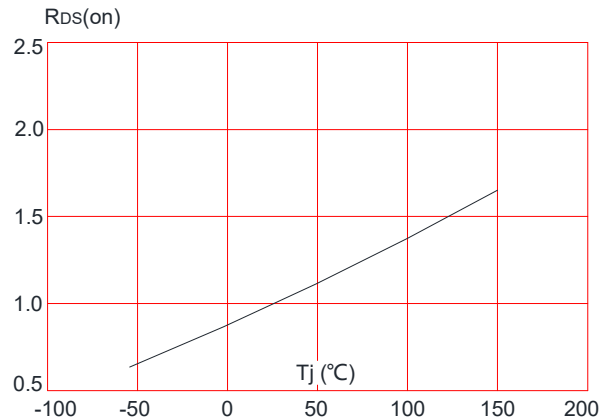


Figure 9: Maximum Safe Operating Area

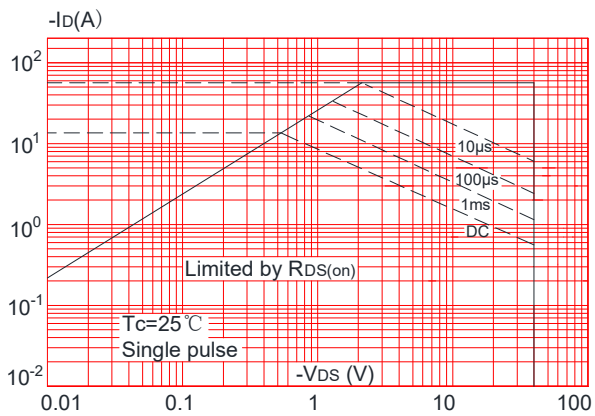


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

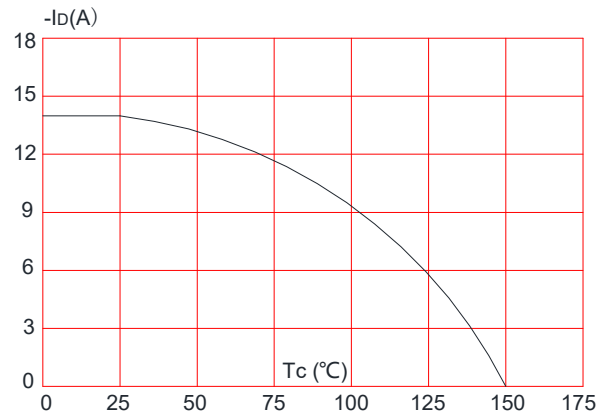
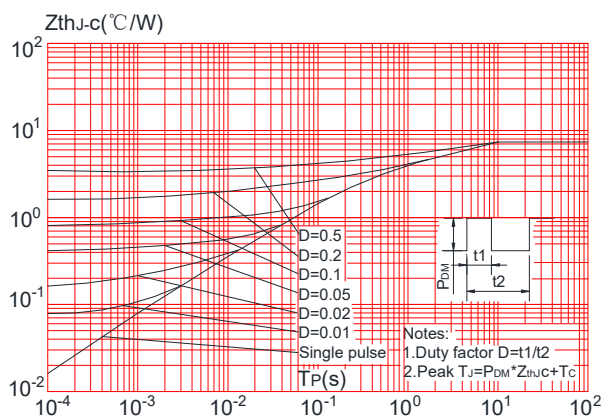
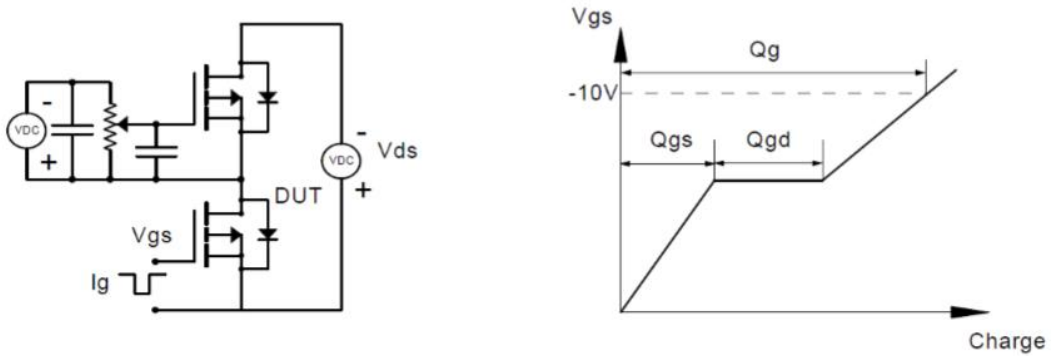


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

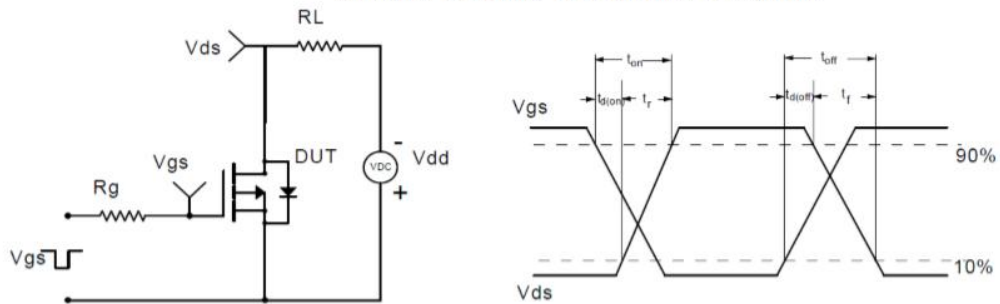


Test Circuit-P

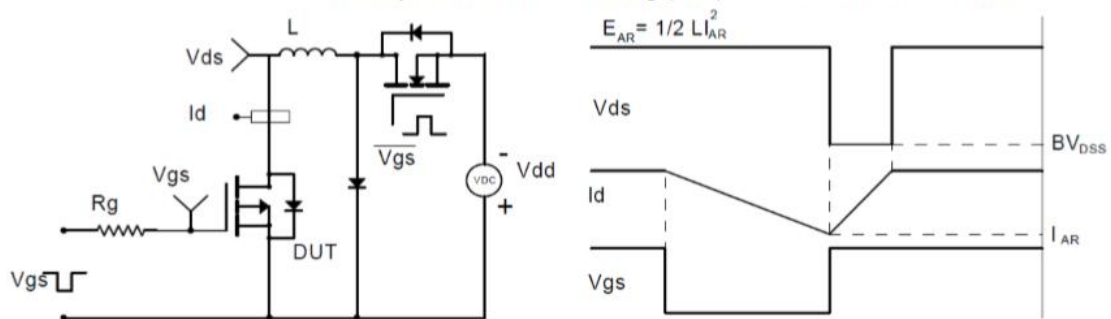
Gate Charge Test Circuit & Waveform



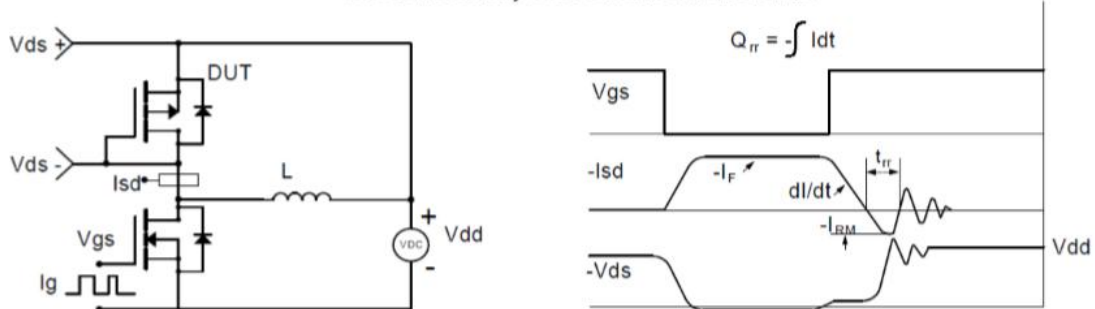
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

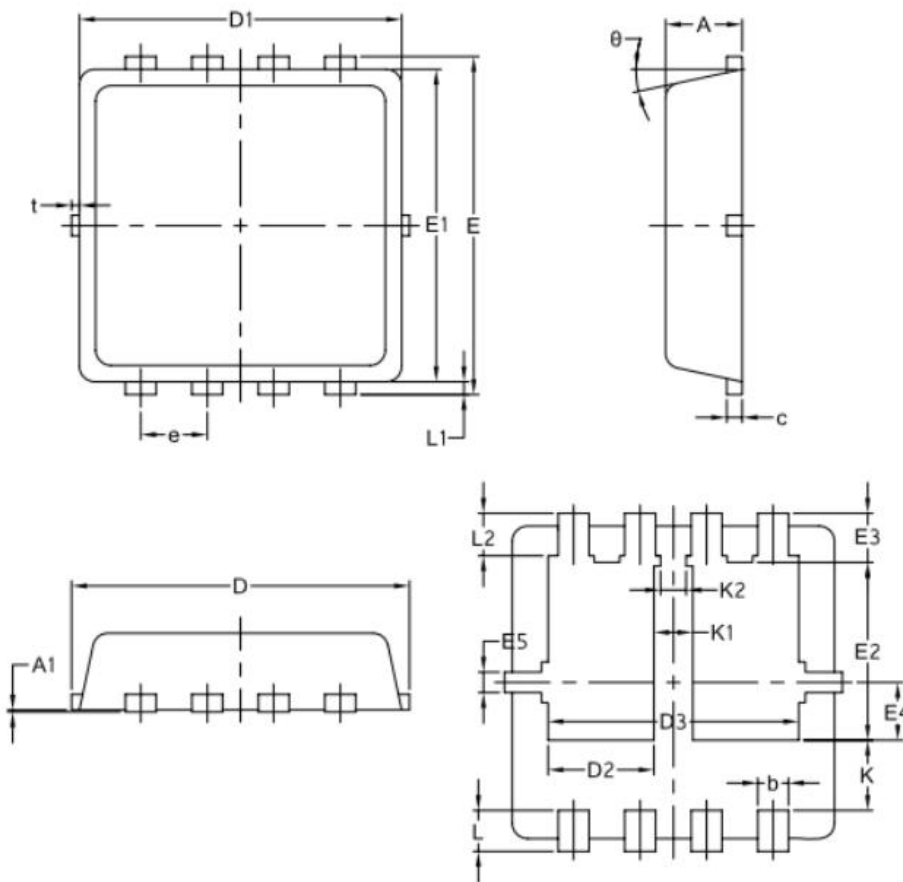


Diode Recovery Test Circuit & Waveforms





Package Mechanical Data- PDFN3.3X3.3-8L



SYMBOL	COMMON		
	MM		
	MIN	NOM	MAX
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
θ	10°	12°	14°

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